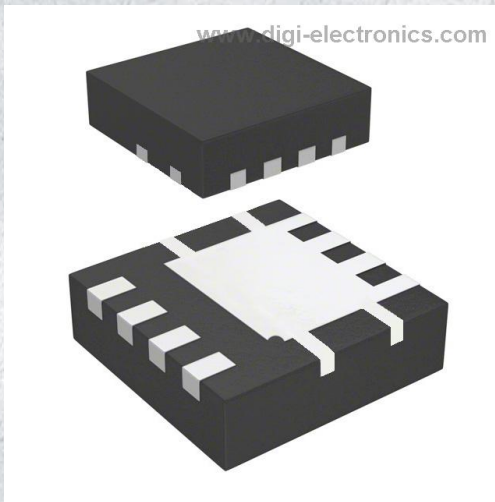


# DMT3004LFG-13 Datasheet



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	DMT3004LFG-13-DG
Manufacturer	<a href="#">Diodes Incorporated</a>
Manufacturer Product Number	DMT3004LFG-13
Description	MOSFET NCH 30V 10.4A POWERDI
Detailed Description	N-Channel 30 V 10.4A (Ta), 25A (Tc) 2.1W (Ta), 42W (Tc) Surface Mount POWERDI3333-8



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

DiGi is a global authorized distributor of electronic components.

## Purchase and inquiry

Manufacturer Product Number:

DMT3004LFG-13

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

30 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

3V @ 250µA

Vgs (Max):

+20V, -16V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Qualification:

AEC-Q101

Supplier Device Package:

PowerDI3333-8

Base Product Number:

DMT3004

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

10.4A (Ta), 25A (Tc)

Rds On (Max) @ Id, Vgs:

4.5mOhm @ 20A, 10V

Gate Charge (Qg) (Max) @ Vgs:

44 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

2370 pF @ 15 V

Power Dissipation (Max):

2.1W (Ta), 42W (Tc)

Grade:

Automotive

Mounting Type:

Surface Mount

Package / Case:

8-PowerVDFN

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMT3004LFG

## N-CHANNEL ENHANCEMENT MODE MOSFET

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_C = +25^\circ C$ (Note 9)
30V	4.5m $\Omega$ @ $V_{GS} = 10V$	25A
	7.0m $\Omega$ @ $V_{GS} = 4.5V$	25A

## Description and Applications

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

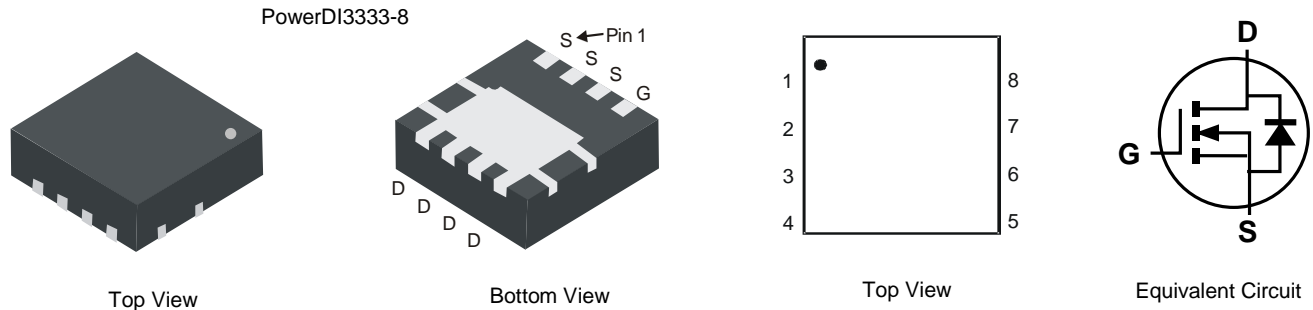
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features and Benefits

- Low  $R_{DS(ON)}$  – Ensures on State Losses Are Minimized
- Excellent  $Q_{gd} \times R_{DS(ON)}$  Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: PowerDI<sup>®</sup> 3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208<sup>(3)</sup>
- Weight: 0.072 grams (Approximate)

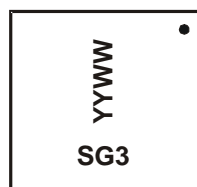


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3004LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT3004LFG-13	PowerDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



SG3 = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 18 = 2018)  
 WW = Week Code (01 to 53)



DMT3004LFG

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	30	V	
Gate-Source Voltage	$V_{GSS}$	+20 -16	V	
Continuous Drain Current (Notes 6 & 9) $V_{GS} = 10\text{V}$	$I_D$	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	25 25	A
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$		$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	10.4 8.3	A
Maximum Continuous Body Diode Forward Current (Note 5)	$I_S$	3	A	
Pulsed Drain Current (10 $\mu\text{s}$ pulse, Duty Cycle = 1%)	$I_{DM}$	95	A	
Avalanche Current, $L=0.3\text{mH}$	$I_{AS}$	27	A	
Avalanche Energy, $L=0.3\text{mH}$	$E_{AS}$	110	mJ	

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	$P_D$	$T_C = +25^\circ\text{C}$	42	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	3	$^\circ\text{C/W}$
Total Power Dissipation (Note 5)	$P_D$	$T_A = +25^\circ\text{C}$	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	60	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$	

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	-	-	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	-	-	100 -100	nA	$V_{GS} = +20\text{V}, V_{DS} = 0\text{V}$ $V_{GS} = -16\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	1	-	3	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	3.5	4.5	m $\Omega$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$
		-	5	7.0		$V_{GS} = 4.5\text{V}, I_D = 7\text{A}$
Diode Forward Voltage	$V_{SD}$	-	0.7	1	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	-	2370	-	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	-	1360	-		
Reverse Transfer Capacitance	$C_{rss}$	-	240	-		
Gate Resistance	$R_g$	-	0.6	-	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_g$	-	20	-	nC	$V_{DS} = 15\text{V}, I_D = 20\text{A}$
Total Gate Charge ( $V_{GS} = 10\text{V}$ )	$Q_g$	-	44	-		
Gate-Source Charge	$Q_{gs}$	-	7	-		
Gate-Drain Charge	$Q_{gd}$	-	8	-		
Turn-On Delay Time	$t_{D(ON)}$	-	6.2	-	ns	$V_{DD} = 15\text{V}, V_{GS} = 10\text{V}, R_L = 0.75\Omega, R_G = 3\Omega, I_D = 20\text{A}$
Turn-On Rise Time	$t_R$	-	4.3	-		
Turn-Off Delay Time	$t_{D(OFF)}$	-	21	-		
Turn-Off Fall Time	$t_F$	-	8	-		
Body Diode Reverse Recovery Time	$t_{RR}$	-	25	-	ns	$I_F = 15\text{A}, di/dt = 500\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	$Q_{RR}$	-	37	-	nC	

- Notes:
- $R_{\theta JA}$  is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1 inch square copper plate.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.
  - Package limited.



**DMT3004LFG**

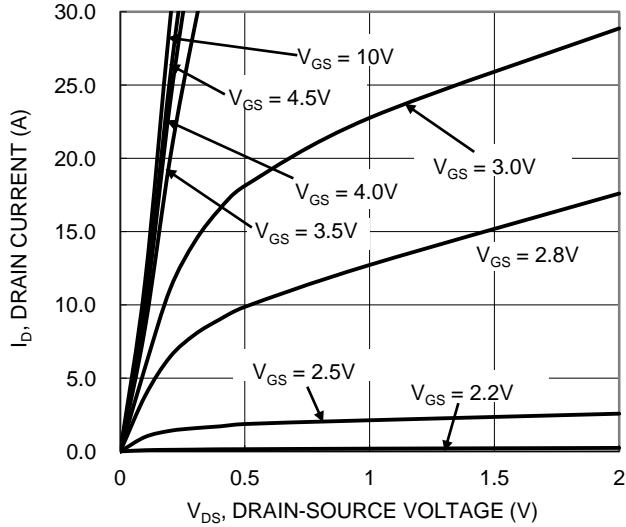


Figure 1. Typical Output Characteristic

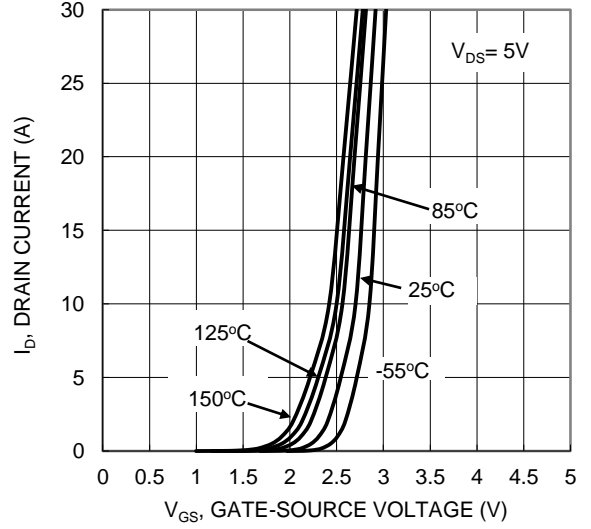


Figure 2. Typical Transfer Characteristic

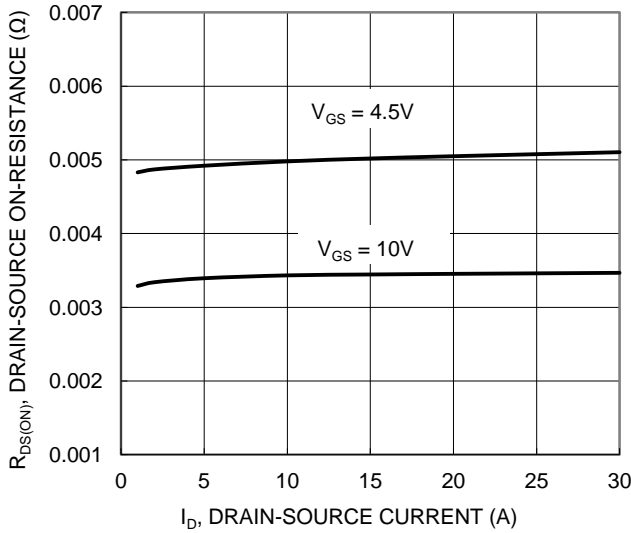


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

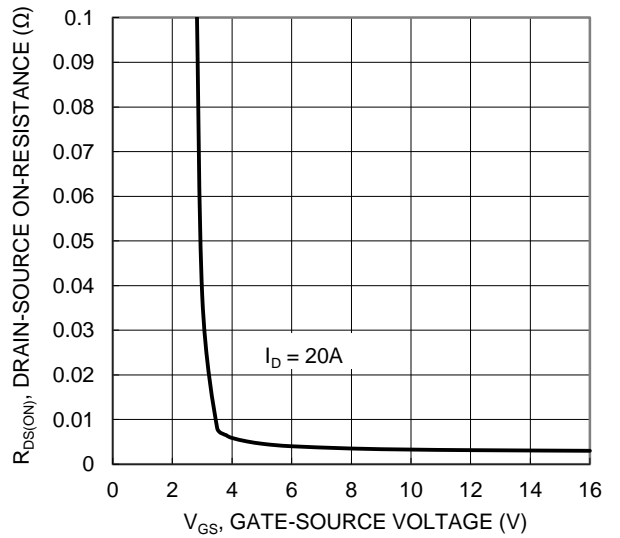


Figure 4. Typical Transfer Characteristic

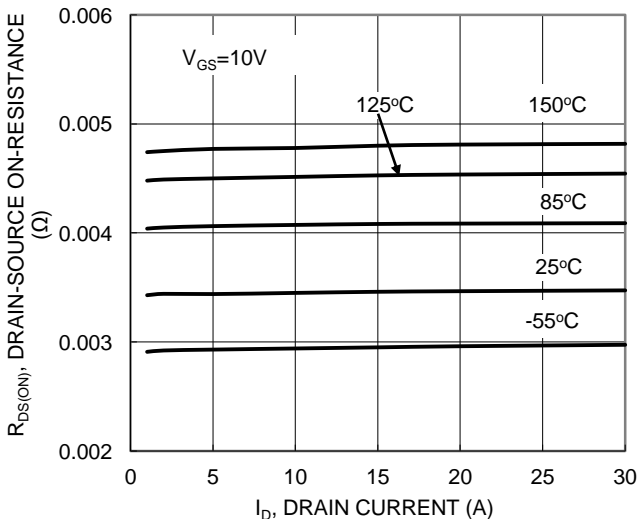


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

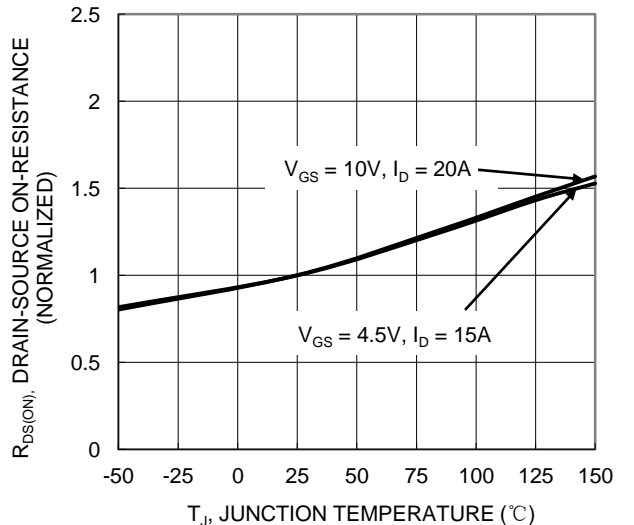


Figure 6. On-Resistance Variation with Junction Temperature



**DMT3004LFG**

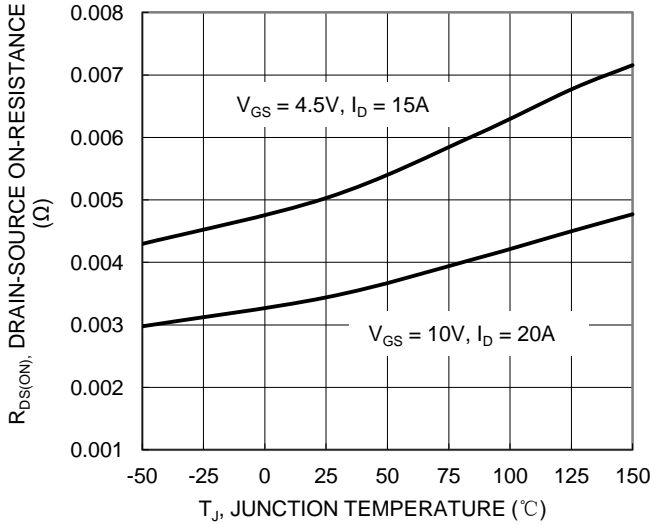


Figure 7. On-Resistance Variation with Junction Temperature

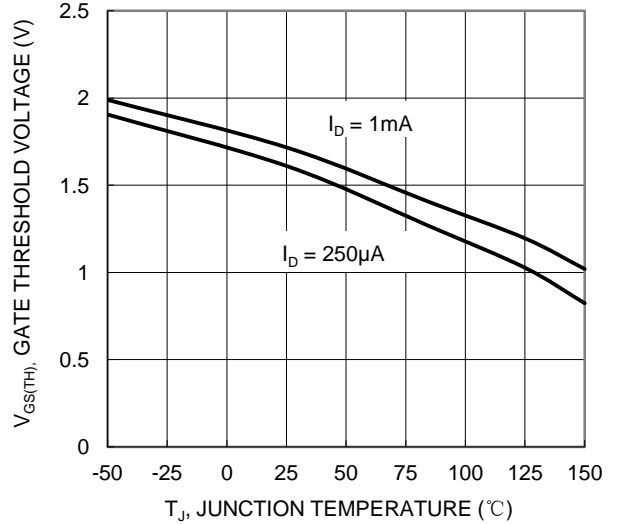


Figure 8. Gate Threshold Variation vs. Junction Temperature

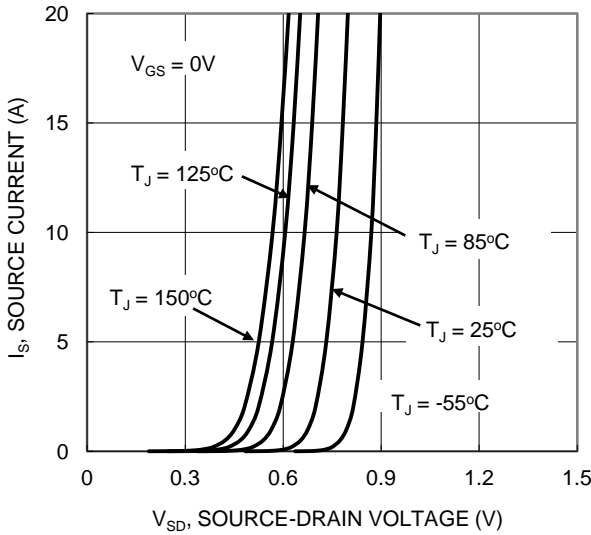


Figure 9. Diode Forward Voltage vs. Current

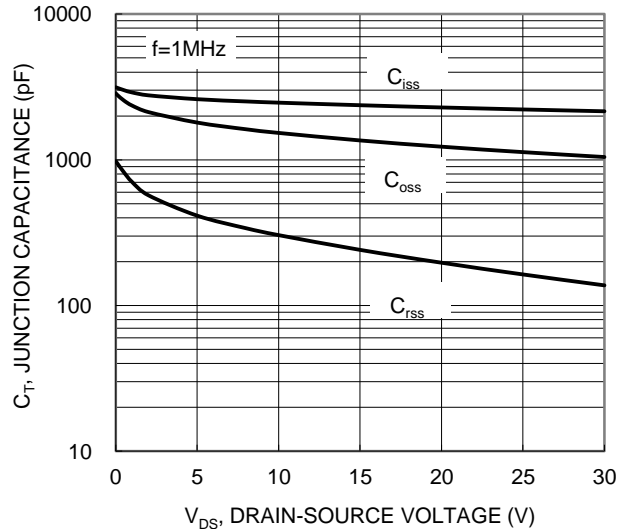


Figure 10. Typical Junction Capacitance

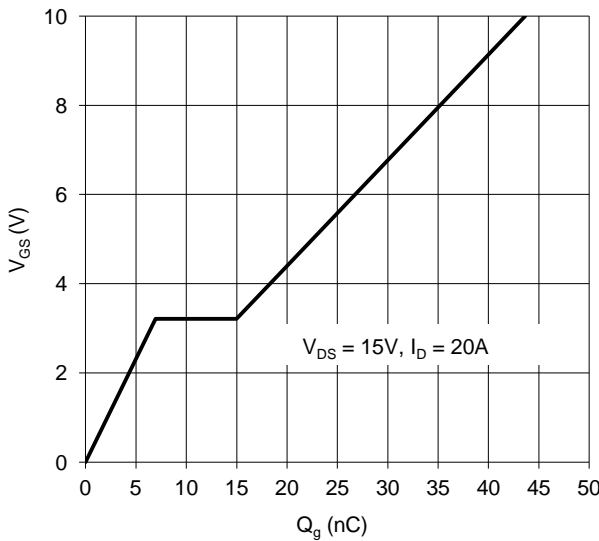


Figure 11. Gate Charge

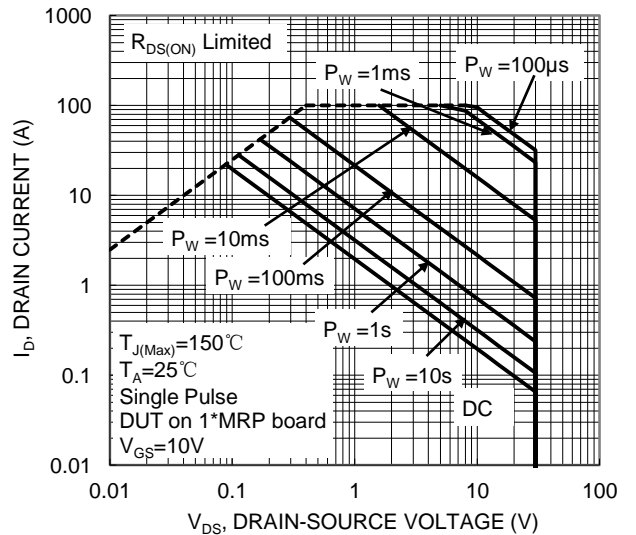


Figure 12. SOA, Safe Operation Area

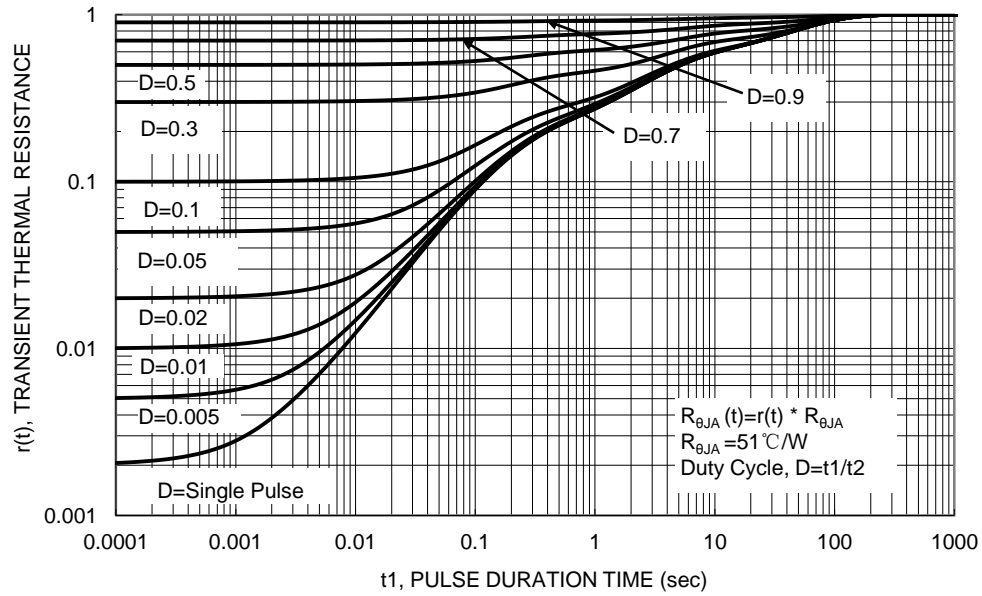
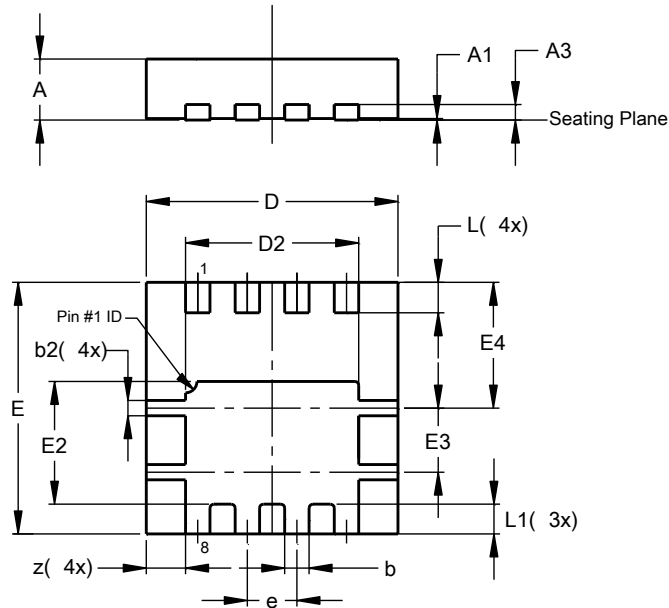


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8

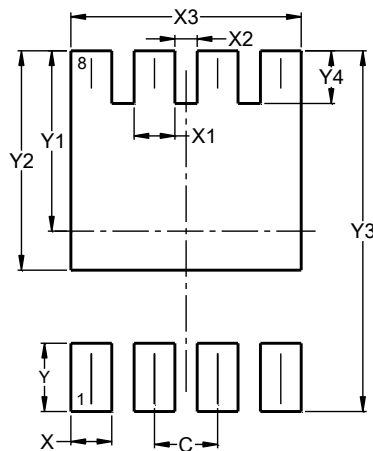


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540





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